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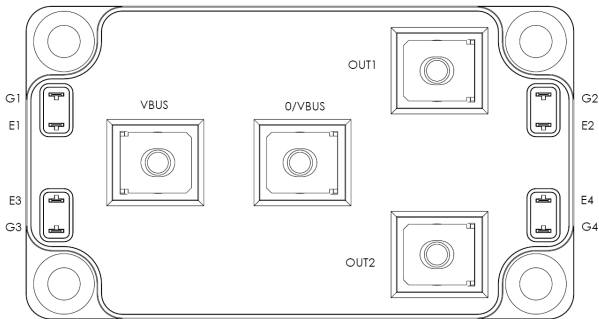
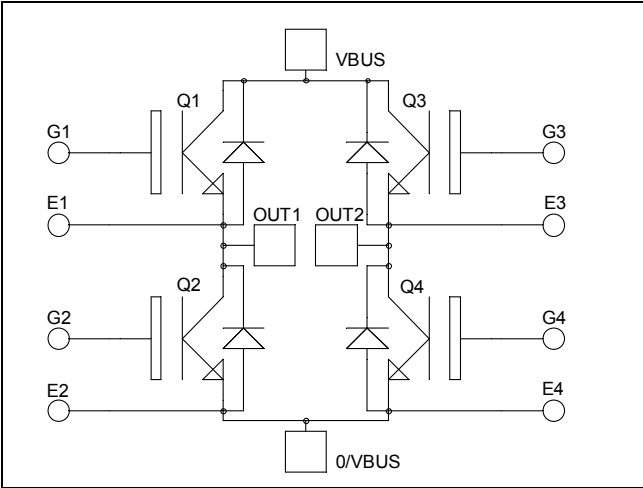
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**Full - Bridge
Trench + Field Stop IGBT3
Power Module**

**$V_{CES} = 600V$
 $I_C = 300A @ T_c = 80^\circ C$**



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- Low profile
- RoHS Compliant

Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|-----------|---------------------------------------|---------------------|-------------|------|
| V_{CES} | Collector - Emitter Breakdown Voltage | | 600 | V |
| I_C | Continuous Collector Current | $T_c = 25^\circ C$ | 430 | A |
| | | $T_c = 80^\circ C$ | 300 | |
| I_{CM} | Pulsed Collector Current | $T_c = 25^\circ C$ | 500 | |
| V_{GE} | Gate - Emitter Voltage | | ± 20 | V |
| P_D | Maximum Power Dissipation | $T_c = 25^\circ C$ | 1150 | W |
| RBSOA | Reverse Bias Safe Operating Area | $T_j = 150^\circ C$ | 600A @ 550V | |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|---------------|--------------------------------------|---|-----|------------|-----|---------------|
| I_{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0\text{V}$, $V_{CE} = 600\text{V}$ | | | 350 | μA |
| $V_{CE(sat)}$ | Collector Emitter Saturation Voltage | $V_{GE} = 15\text{V}$ $I_C = 300\text{A}$ | | 1.4 1.5 | 1.8 | V |
| $V_{GE(th)}$ | Gate Threshold Voltage | $V_{GE} = V_{CE}$, $I_C = 1.5\text{ mA}$ | 5.0 | 5.8 | 6.5 | V |
| I_{GES} | Gate – Emitter Leakage Current | $V_{GE} = 20\text{V}$, $V_{CE} = 0\text{V}$ | | | 500 | nA |

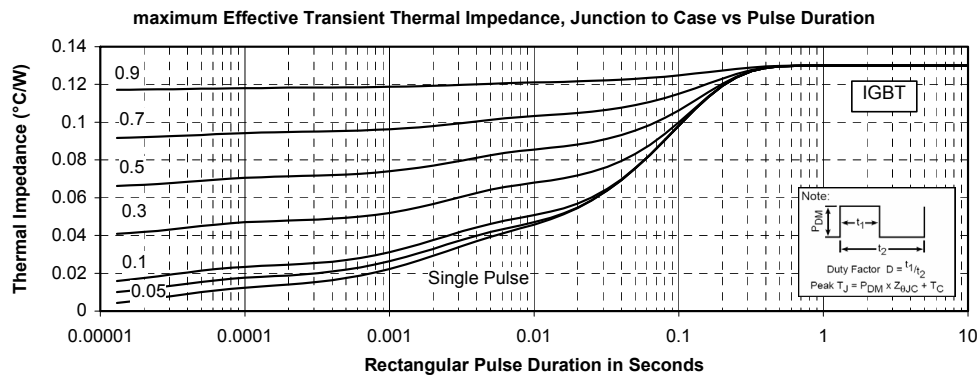
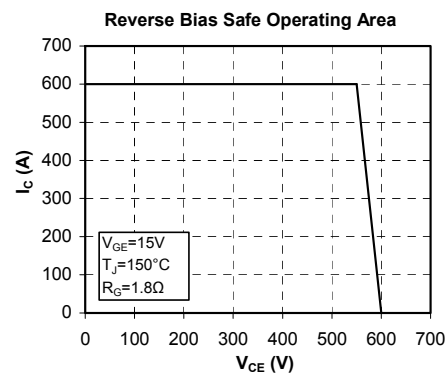
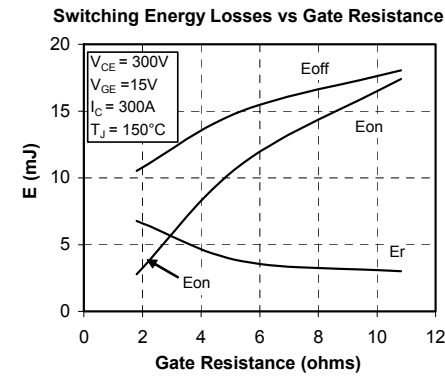
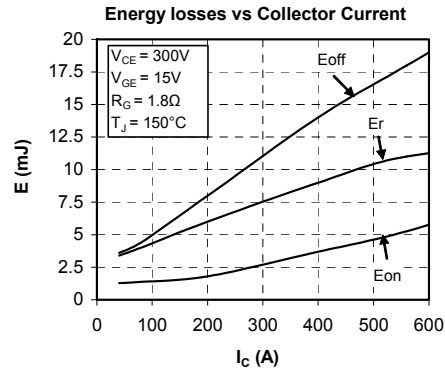
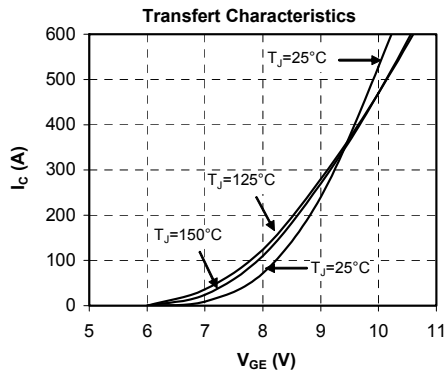
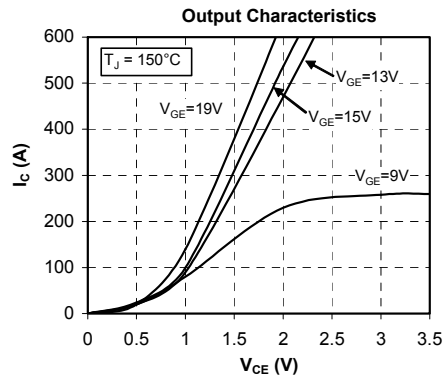
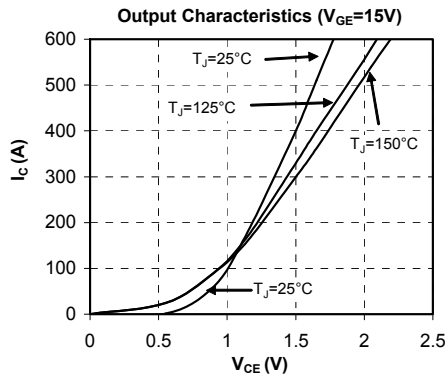
Dynamic Characteristics

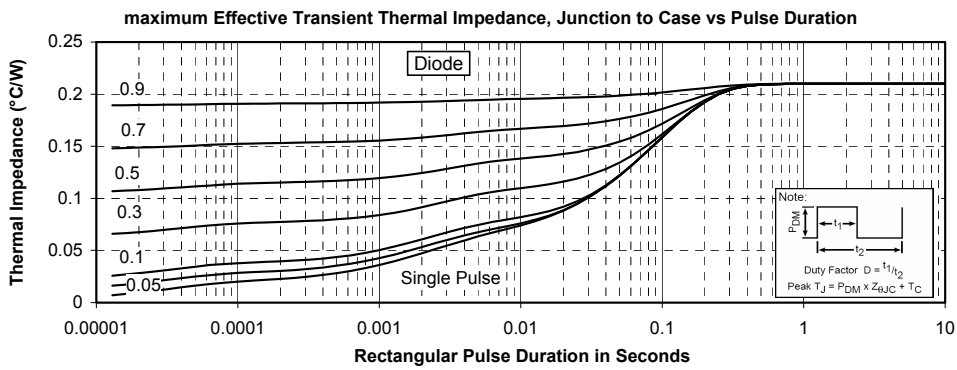
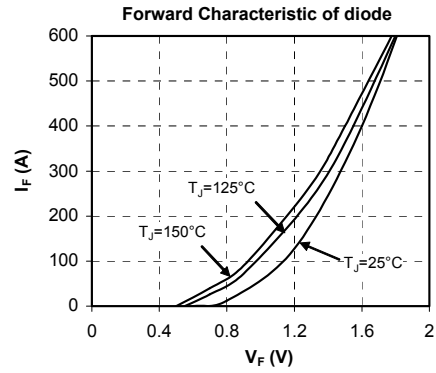
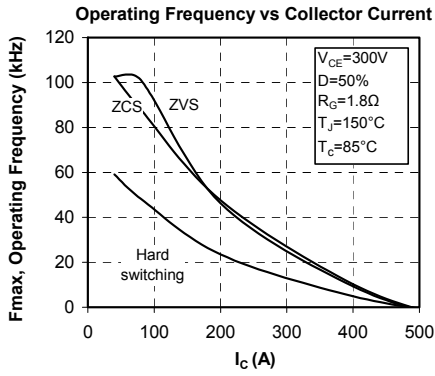
| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|--------------|------------------------------|--|---|--------------|-----|------|
| C_{ies} | Input Capacitance | $V_{GE} = 0\text{V}$ | | 24 | | nF |
| C_{oes} | Output Capacitance | $V_{CE} = 25\text{V}$ | | 1.5 | | |
| C_{res} | Reverse Transfer Capacitance | $f = 1\text{MHz}$ | | 0.75 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (25°C) | | 115 | | ns |
| T_r | Rise Time | $V_{GE} = \pm 15\text{V}$ | | 45 | | |
| $T_{d(off)}$ | Turn-off Delay Time | $V_{Bus} = 300\text{V}$ $I_C = 300\text{A}$ | | 200 | | |
| T_f | Fall Time | $R_G = 1.8\Omega$ | | 55 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (150°C) | | 120 | | ns |
| T_r | Rise Time | $V_{GE} = \pm 15\text{V}$ | | 50 | | |
| $T_{d(off)}$ | Turn-off Delay Time | $V_{Bus} = 300\text{V}$ $I_C = 300\text{A}$ | | 250 | | |
| T_f | Fall Time | $R_G = 1.8\Omega$ | | 70 | | |
| E_{on} | Turn on Energy | $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ | $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ | 1.5 2.7 | | mJ |
| E_{off} | Turn off Energy | $I_C = 300\text{A}$ $R_G = 1.8\Omega$ | $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ | 8.55 10.5 | | mJ |

Reverse diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|-----------|---|--|---|--------------|------------|---------------|
| V_{RRM} | Maximum Peak Repetitive Reverse Voltage | | 600 | | | V |
| I_{RM} | Maximum Reverse Leakage Current | $V_R = 600\text{V}$ | | | 150 400 | μA |
| I_F | DC Forward Current | | | 300 | | A |
| V_F | Diode Forward Voltage | $I_F = 300\text{A}$ $V_{GE} = 0\text{V}$ | | 1.5 1.4 | 1.9 | V |
| t_{rr} | Reverse Recovery Time | | $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ | 130 225 | | ns |
| Q_{rr} | Reverse Recovery Charge | $I_F = 300\text{A}$ $V_R = 300\text{V}$ $di/dt = 3100\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ | 13.5 28.5 | | μC |
| E_r | Reverse Recovery Energy | | $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$ | 3.5 7.1 | | mJ |

Typical Performance Curve





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